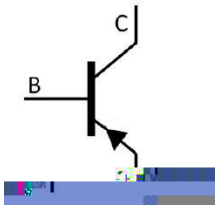
TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

High breakdown voltage, high current, low saturation voltage.

Low frequency power amplifier applications.



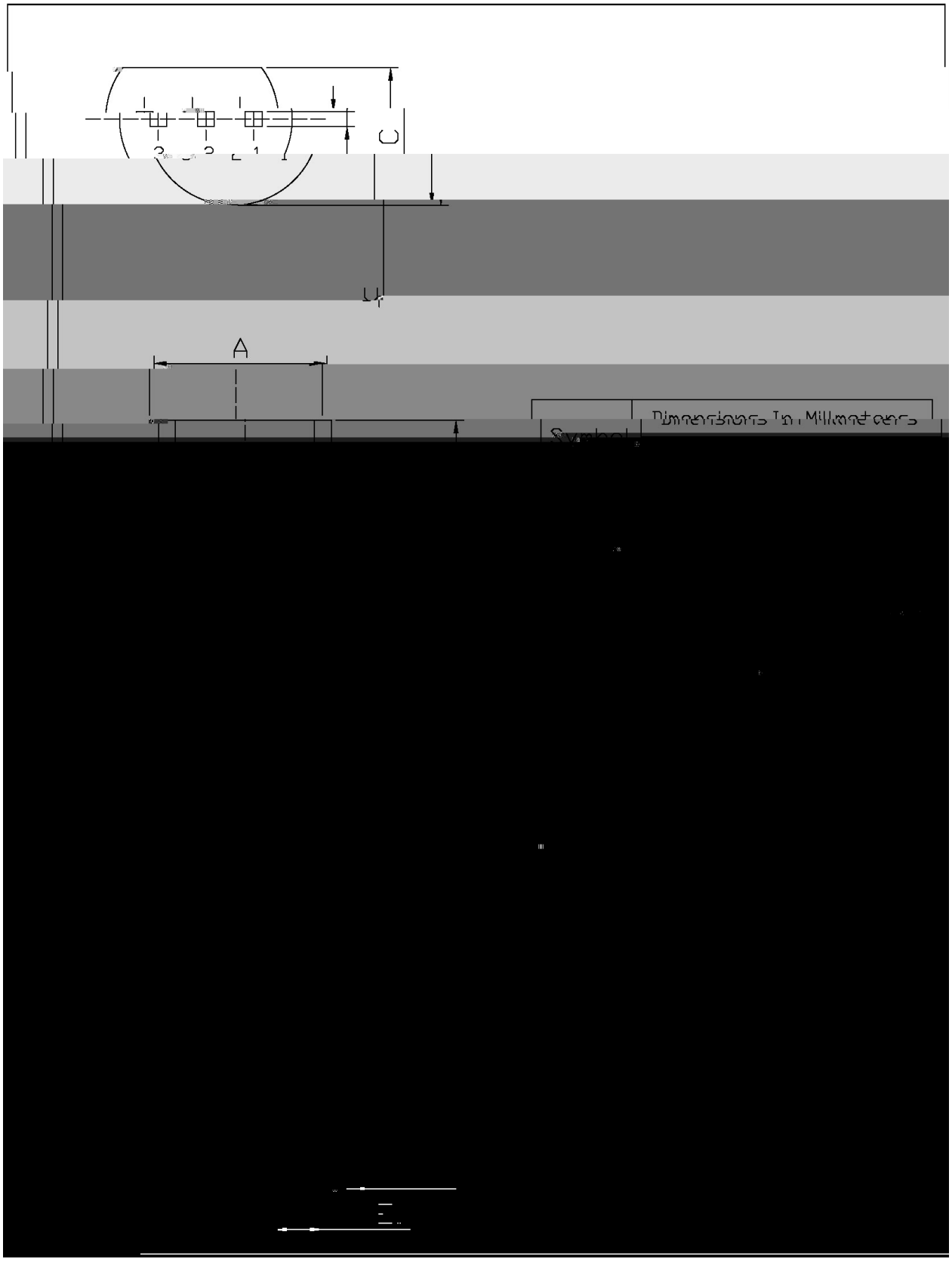
PIN1 Base PIN 2 Collector PIN 3 Emitter

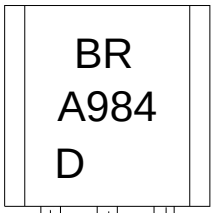
h_{FE} Classifications Symbol	D	E	F
h_{FE} Range	60~120	100~200	160~320

Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SA984	-60	V
		2SA984K	-100	
Collector to Emitter Voltage	V_{CEO}	2SA984	-50	V
		2SA984K	-80	
Emitter to Base Voltage	V_{EBO}		-5.0	V
Collector Current - Continuous	I_C		-500	mA
Collector Current – Continuous(Pulse)	I_{CP}		-800	mA
Collector Power Dissipation	P_C		600	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

Parameter	Symbol		Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	2SA984	I_C=-10μA I_E=0	-60			V
		2SA984K		-100			
Collector to Emitter Breakdown Voltage	V_{CEO}	2SA984	I_C=-1.0mA R_{BE}=∞	-50			V
		2SA984K		-80			
Emitter to Base Breakdown Voltage	V_{EBO}		I_E=-10μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}		V_{CB}=-40V I_E=0			-1.0	μA
Emitter Cutoff Current	I_{EBO}		V_{EB}=-4.0V I_C=0			-1.0	μA
DC Current Gain	$h_{FE(1)}$		V_{CE}=-5.0V I_C=-50mA	60		320	
	$h_{FE(2)}$		V_{CE}=-5.0V I_C=-400mA	35			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		I_C=-400mA I_B=-40mA		-0.25	-0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$		I_C=-400mA I_B=-40mA		-0.9	-1.2	V
Transition Frequency	f_T		V_{CE}=-10V I_C=-10mA		120		MHz
Collector Output Capacitance	C_{ob}		V_{CB}=-10V f=1.0MHz		9.0		pF

TO-92 Unit: mm





BR:

A984

D: h_{FE}

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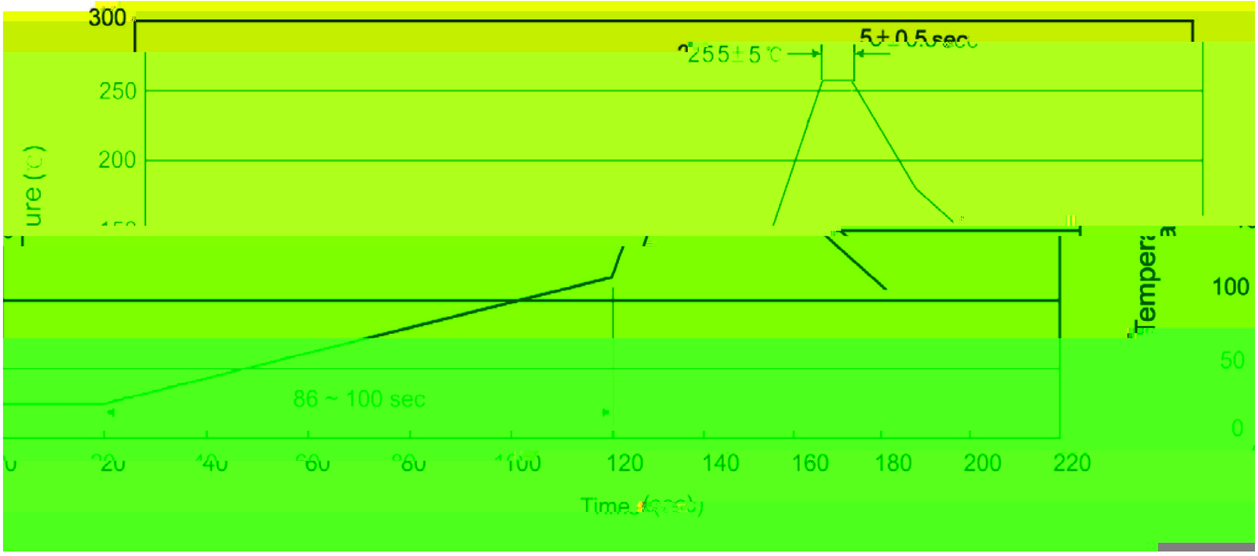
Note:

BR:	Company Code.
A984:	Product Type.
D:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.



Note:

1 25 150 60 90sec;
1.Preheating:25~150 , Time:60~90sec.

2 255±5 5±0.5sec;
2.Peak Temp.:255±5 , Duration:5±0.5sec.

3 2 10 /sec.
3. Cooling Speed: 2~10 /sec.

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ BULK

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